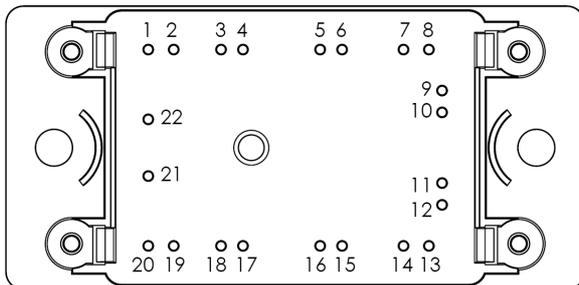
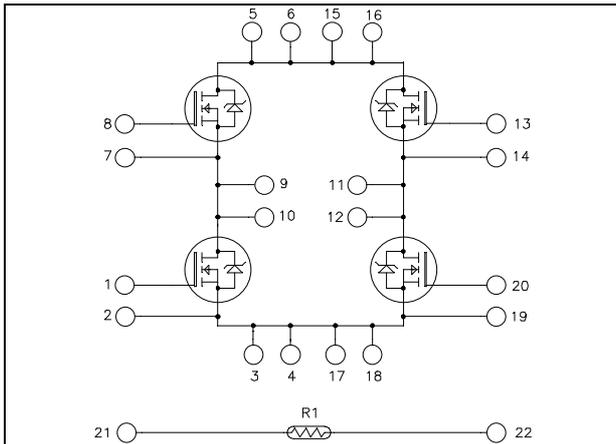


## Full - Bridge Super Junction MOSFET Power Module

$V_{DSS} = 900V$   
 $R_{DSon} = 120m\Omega \text{ max @ } T_j = 25^\circ C$   
 $I_D = 30A \text{ @ } T_c = 25^\circ C$



Pins 5/6/15/16 ; 3/4/17/18 ; 9/10 ; 11/12 must be shorted together

### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

- CoolMOST™
  - Ultra low  $R_{DSon}$
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
  - Very rugged
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

All ratings @  $T_j = 25^\circ C$  unless otherwise specified

### Absolute maximum ratings (per CoolMOST™)

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	900	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	30
		$T_c = 80^\circ C$	23
$I_{DM}$	Pulsed Drain current	75	A
$V_{GS}$	Gate - Source Voltage	$\pm 20$	V
$R_{DSon}$	Drain - Source ON Resistance	120	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	250
$I_{AR}$	Avalanche current (repetitive and non repetitive)	8.8	A
$E_{AR}$	Repetitive Avalanche Energy	2.9	mJ
$E_{AS}$	Single Pulse Avalanche Energy	1940	

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

**Electrical Characteristics** (per CoolMOST™)

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 900V	T <sub>j</sub> = 25°C			100	μA
		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 900V	T <sub>j</sub> = 125°C		500		
R <sub>DS(on)</sub>	Drain – Source on Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 26A			100	120	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 3mA		2.5	3	3.5	V
I <sub>GSS</sub>	Gate – Source Leakage Current	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0V				100	nA

**Dynamic Characteristics** (per CoolMOST™)

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0V ; V <sub>DS</sub> = 100V f = 1MHz			6.8		nF
C <sub>oss</sub>	Output Capacitance				0.33		
Q <sub>g</sub>	Total gate Charge	V <sub>GS</sub> = 10V V <sub>Bus</sub> = 400V I <sub>D</sub> = 26A			270		nC
Q <sub>gs</sub>	Gate – Source Charge				32		
Q <sub>gd</sub>	Gate – Drain Charge				115		
T <sub>d(on)</sub>	Turn-on Delay Time	<b>Inductive Switching (125°C)</b> V <sub>GS</sub> = 10V V <sub>Bus</sub> = 600V I <sub>D</sub> = 26A R <sub>G</sub> = 7.5Ω			70		ns
T <sub>r</sub>	Rise Time				20		
T <sub>d(off)</sub>	Turn-off Delay Time				400		
T <sub>f</sub>	Fall Time				25		
E <sub>off</sub>	Turn-off Switching Energy	<b>Inductive switching</b> V <sub>GS</sub> = 10V; I <sub>D</sub> = 26A V <sub>Bus</sub> = 600V; R <sub>G</sub> = 7.5Ω		T <sub>j</sub> = 25°C	0.75		mJ
E <sub>off</sub>	Turn-off Switching Energy			T <sub>j</sub> = 125°C	0.85		mJ
R <sub>thJC</sub>	Junction to Case Thermal Resistance					0.5	°C/W

**Source - Drain diode ratings and characteristics** (per CoolMOST™)

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
I <sub>S</sub>	Continuous Source current (Body diode)			T <sub>c</sub> = 25°C		30	A
				T <sub>c</sub> = 80°C		23	
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = - 26A			0.8	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> = - 26A V <sub>R</sub> = 400V	T <sub>j</sub> = 25°C		920		ns
Q <sub>rr</sub>	Reverse Recovery Charge	di <sub>S</sub> /dt = 200A/μs	T <sub>j</sub> = 25°C		30		μC

## Temperature sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		22		kΩ
ΔR <sub>25</sub> /R <sub>25</sub>	Resistance tolerance			5	%
ΔB/B	Beta tolerance			3	
B <sub>25/100</sub>	T <sub>25</sub> = 298.16 K		3980		K

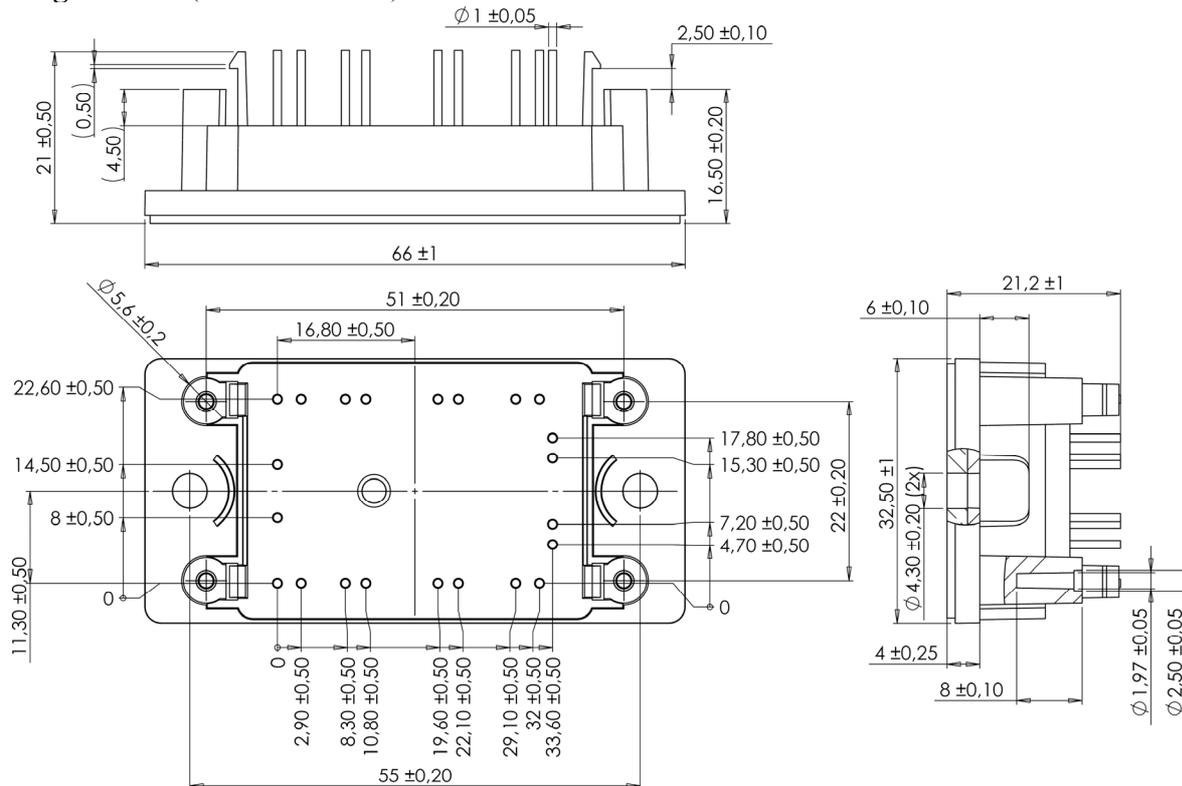
$$R_T = \frac{R_{25}}{\exp\left[B_{25/100}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

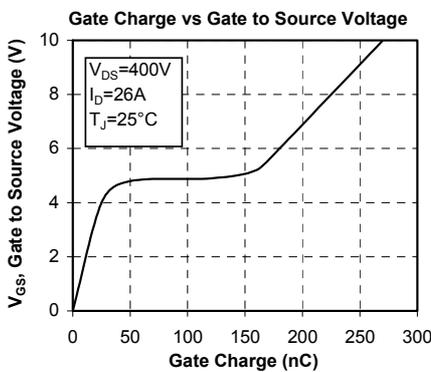
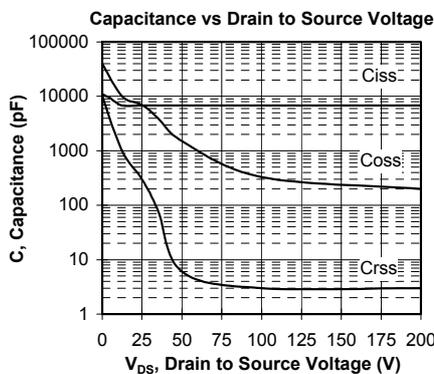
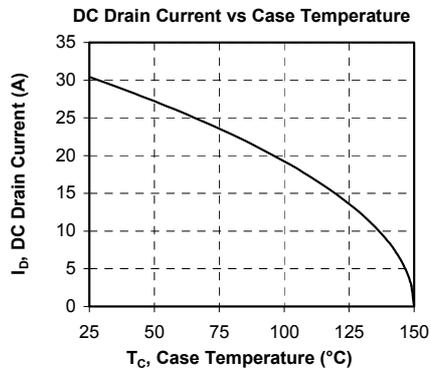
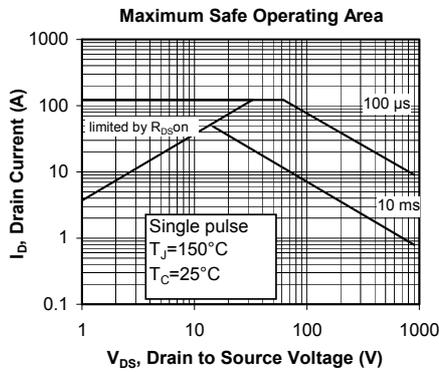
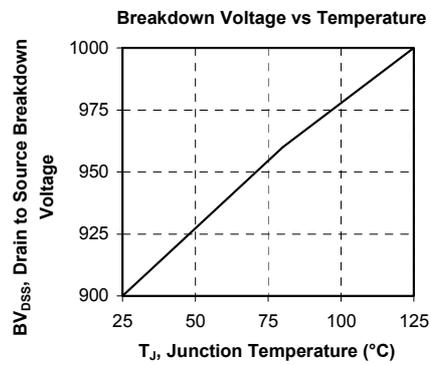
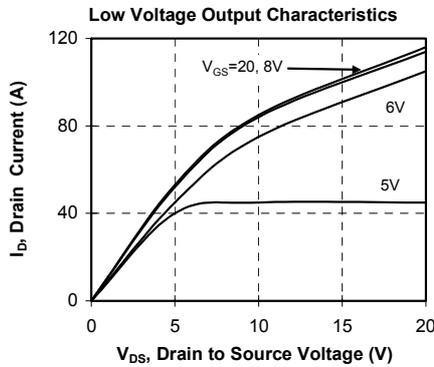
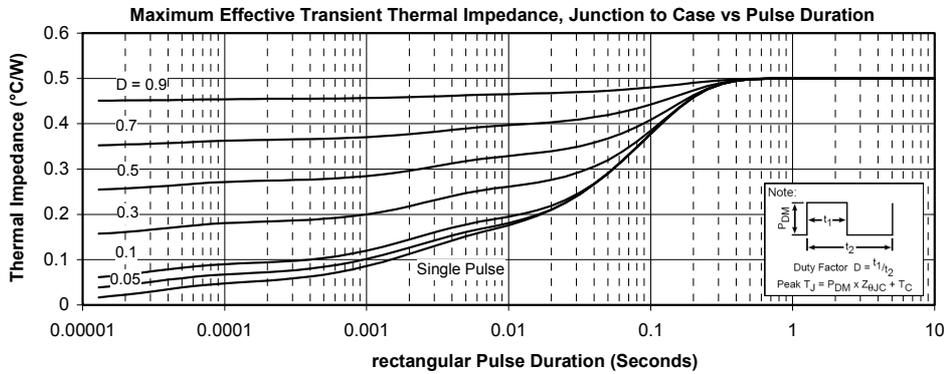
## Thermal and package characteristics

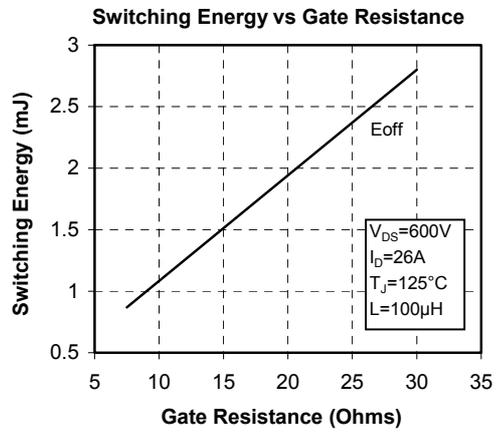
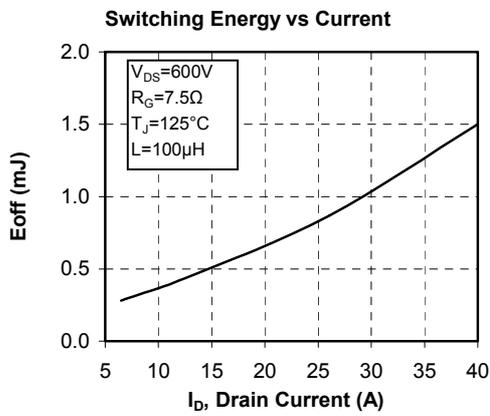
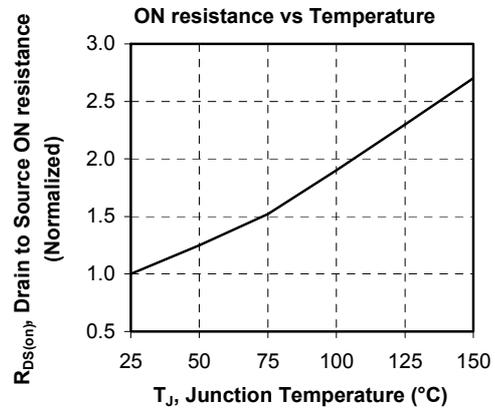
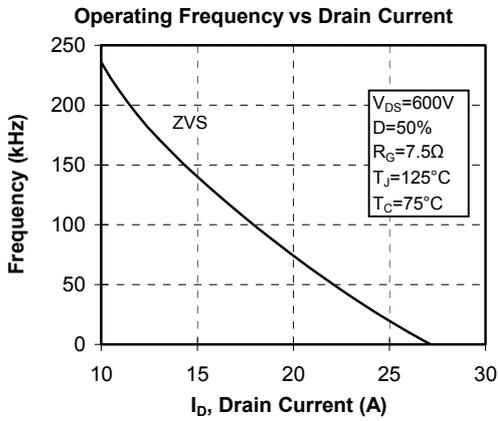
Symbol	Characteristic	Min	Typ	Max	Unit	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000			V	
T <sub>J</sub>	Operating junction temperature range	-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				75	g

## Package outline (dimensions in mm)



## Typical performance Curve (per CoolMOST™)





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